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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
08/811,742	03/06/1997	HONGYONG ZHANG	0756-1641	1505
22204	7590	10/28/2003	EXAMINER	
NIXON PEABODY, LLP 8180 GREENSBORO DRIVE SUITE 800 MCLEAN, VA 22102			NGUYEN, KHIEM D	
			ART UNIT	PAPER NUMBLR
			2823	

DATE MAILED: 10/28/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	08/811,742	ZHANG ET AL. <i>W</i>	
	Examiner	Art Unit	
	Khiem D Nguyen	2823	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 49-66 and 85-120 is/are pending in the application.
- 4a) Of the above claim(s) 49-66 is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 85-120 is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 05 June 1995 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on ____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. ____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s) ____. |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) ____. | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 09-24-2003 has been entered. A new rejection is made as set forth in this Office Action. Claims (85-120) are pending in the application.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 85-87, 90-93, 96-99, 102-105, 108-111, 114-117, and 120 are rejected under 35 U.S.C. 102(b) as being anticipated by Oka (JP-140915) (translation).

In re claims 85, 91, 97, 103, 109, 115, Oka discloses a method for manufacturing a semiconductor device comprising the steps of: forming a semiconductor film over a substrate (page 6, translation); disposing a crystallizing promoting material in contact with a selected portion of the semiconductor film (page 14, translation); crystallizing the semiconductor film by heating (pages 6-7, translation), patterning the crystalline semiconductor film to an active layer including the selected portion (FIG. 1(d)); forming

a gate insulating film (FIG. 1 (d), element 108) over the active layer, forming a gate electrode (FIG. 1(d), element 106) over the gate insulating film; forming an insulating film (FIG. 1(d), element 109) over the gate insulating film; and forming a wiring (FIG. 1(d), 111) over the insulating film, wherein the wiring is connected to the selected portion and wherein the crystals extend along with a direction in which carriers of the thin film transistor flow (FIGS. 1(b)-8 and related text).

Additionally, Oka discloses forming two gate electrodes (FIG. 1(d), 1st gate electrode (106) and the second gate electrode (unlabeled)) over the gate insulating film (FIG. 1(d), 108) wherein the active layer constitutes a pair of N-channel and P-channel thin film transistors and wherein the crystals extend along with a direction connecting source and drain regions of the thin film transistor (FIG. 1(b)-8).

In re claims 86, 92, 98, 104, 110, and 116, Oka discloses wherein the crystallization promoting material comprises an element selected from the group consisting of Ni and Pt (page 14, translation).

In re claims 87, 93, 99, 105, 111, and 117, Oka discloses method according to claim 85, wherein the heating is performed at a temperature of approximately 200° C to 450° C (pages 6-7, translation).

In re claims 90, 96, 102, 108, 114, and 120, Oka discloses wherein the semiconductor device constitutes a driver circuit of an active matrix display device (FIGS. 1(b)-8 and related text).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claim 88, 89, 94, 95, 100, 101, 106, 107, 112, 113, 118, and 119 are rejected under 35 U.S.C. 103(a) as being unpatentable over Oka (JP-140915) (translation) as applied to claims 85-87, 90-93, 96-99, 102-105, 108-111, 114-117, and 120 above, and further in view of Kuznetsov ((Inst. Phys. Conf) pages 191-194).

In re claims 89, 95, 101, 107, 113, and 119, Kuznetsov discloses that metal catalyst induced crystallization occurs by lateral diffusion of the metal throughout the a-Si film. In addition, Kuznetsov teaches a concentration of Ni⁺ ions to a maximum concentration of about 1.5×10^{20} atoms/cm³ (pages, 191-194) Thus, such diffusion, while not explicitly taught by Oka, is inherent in the process of Oka as a result of the metal induced lateral crystallization. It would have been obvious to one of ordinary skill in the art of making semiconductor devices to combine the teaching of Oka and Kuznetsov to enable the active layer contains the crystallization promoting material at a concentration of 1×10^{15} atoms/cm³ or more of Oka to be formed and furthermore an enhanced rate of crystallization can be obtained (Abstract).

In re claims 88, 94, 100, 106, 112, and 118, the process wherein the crystallization promoting material is disposed by a spin-coating is well-known to one of ordinary skill in the art of making semiconductor devices.

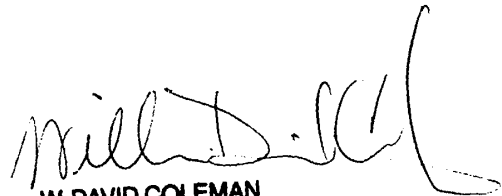
Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (703) 306-0210. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 746-9179 for regular communications and (703) 746-9179 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

K.N.
October 20, 2003


W. DAVID COLEMAN
PRIMARY EXAMINER